

Please amend the claims as indicated below:

**1. (Previously Presented)** An ion-assisted electron beam evaporation process, the process comprising the steps of:

- positioning multiple high yield fixtures in an array;
- adjusting a vertical position of each of the fixtures to compensate for variations in deposition rate versus chamber location;
- providing two electron guns;
- mounting the guns to a movable track;
- positioning the first gun at a source deposition location;
- rotating the fixtures at greater than 2400 rpm;
- performing ion assisted evaporation with the first gun, the second gun being kept in a stand-by location in pre-heat mode;
- ceasing deposition prior to achieving target thickness on each fixture by shuttering each of the fixtures;
- independently reopening the fixtures to resume deposition at a low rate pulsed deposition to achieve the target thickness;
- closing shutters on the fixtures;
- moving the first gun to a stand-by position;
- moving the second gun to the source deposition location;
- sampling evaporation with a quartz crystal thickness monitor;
- opening a shutter on the second gun;

performing ion assisted evaporation with the second gun, the first gun being kept in a stand-by location in pre-heat mode;

ceasing deposition prior to achieving target thickness shuttering each of the fixtures;

independently reopening the fixtures to resume deposition at a low rate pulsed deposition to achieve the target thickness;

closing shutters on the fixtures; and

repeating the process until desired filter is obtained.

**2. (Currently Amended)** A method for producing an optical filter utilizing line-of-sight deposition, the method comprising the steps of:

providing multiple substrates;

providing a fixed ion source;

providing at least one selectively movable evaporator, the evaporator providing energy for evaporation of material to be deposited and being positionable at a source deposition location and at a stand-by location ~~laterally spaced from the source deposition location, the stand-by location being laterally spaced from the ion source a distance greater than the distance the source deposition location is spaced from the ion source;~~

positioning the at least one evaporator at the source deposition location; and,

depositing material onto the substrates .

**3. (Original)** The method of Claim 2, wherein the method further comprises the step of:

shuttering the substrates as necessary to ensure uniform deposition on the substrates.

4. **(Original)** The method of Claim 3, where in the method further comprises the step of:

rotating the substrates at approximately greater than 500 revolutions per minute.

5. **(Previously Presented)** The method of Claim 4, wherein shuttering the substrates as necessary to ensure uniform deposition on the substrates comprises the steps of:

ceasing deposition of a layer prior to achieving target thickness by shuttering the substrates;

independently unshuttering the substrates to resume deposition; and,  
achieving the target thickness.

6. **(Previously Presented)** The method of Claim 2, wherein the at least one evaporator is at least two selectively movable evaporators, the method further comprising the steps of:

moving the first evaporator to the stand-by position;  
opening a shutter on the second evaporator;  
positioning the second evaporator at the source deposition location; and,  
performing ion assisted evaporation with the second evaporator.

7. **(Previously Presented)** The method of Claim 6, wherein the method further comprises the steps of:

ceasing deposition of a layer prior to achieving target thickness by shuttering the substrates;

independently unshuttering the substrates to resume deposition; and,  
achieving the target thickness.

**8. (Original)** The method of Claim 7, wherein after moving the second evaporator into the source deposition location, the method comprises the step of:  
sampling evaporation with a quartz crystal thickness monitor.

**9. (Original)** The method of Claim 8, wherein the method further comprises the steps of:

closing clam shutters on the substrates; and,  
repeating the process until desired filter is obtained.

**10. (Original)** The method of Claim 9, wherein providing multiple substrates comprises the step of:

providing a dense high yield fixture array having multiple, independently shutterable fixtures, each of the fixtures containing multiple substrates.

**11-19. (Canceled)**

**20. (Original)** The method of Claim 4, wherein rotating the substrates at greater than 500 revolutions per minute comprises the step of:

rotating the substrates at greater than 2400 revolutions per minute.

**21-22. (Canceled)**

**23. (Currently Amended)** A method of making an optical filter by ion assisted deposition comprising the steps of:

mounting one or more substrates in a deposition chamber;

mounting an ion source within the chamber;

positioning a first evaporator at a source deposition position located within the chamber proximate the ion source, the first evaporator being adapted to provide energy for evaporation of a first material to be deposited;

positioning a second evaporator at a standby position located within the chamber remote from the ion source ~~and laterally spaced from the source deposition position,~~ the second evaporator being adapted to provide energy for evaporation of a second material to be deposited;

depositing a first material from the first evaporator on the one or more substrates;

ceasing deposition of the first material;

positioning the first evaporator at a standby position within the chamber remote from the ion source ~~and laterally spaced from the source deposition position;~~

positioning the second evaporator at the source deposition position ~~laterally spaced from the stand-by position;~~

depositing a second material from the second evaporator on the one or more substrates; and

ceasing deposition of the second material.

**24. (Currently Amended)** A method of making an optical filter by ion assisted deposition comprising the steps of:

exposing one or more substrates to a first evaporator adapted to provide energy to evaporate a first material to be deposited positioned at a source deposition location;

shielding the one or more substrates from a second evaporator positioned at a standby location laterally spaced from the source deposition location;

depositing a layer of a first material on the one or more substrates;

exposing the one or more substrates to the second evaporator adapted to provide energy to evaporate a second material to be deposited positioned at the source deposition location;

shielding the one or more substrates from the first evaporator positioned at the standby location; and

depositing a layer of second material on the one or more substrates.

**25. (Currently Amended)** A method comprising the steps of:

providing a deposition chamber;

positioning a generally planar substrate carrier proximate one end of the chamber, the substrate carrier being adapted to carry an array of substrates;

positioning a generally planar ~~target~~ electron gun carrier proximate the other end of the chamber, the ~~target~~ electron gun carrier being substantially parallel to the substrate carrier;

providing a source deposition location on the ~~target~~ electron gun carrier;

providing a stand-by location on the ~~target~~ electron gun carrier, the stand-by location being spaced laterally from the source deposition location;

positioning a ~~target~~ an electron gun on the ~~target~~ electron gun carrier, the ~~target~~ electron gun being adapted to provide energy for evaporation of material to be deposited

on the substrates and being positionable at the source deposition location and the stand-by location; and

positioning an ion source proximate the source deposition location.

**26. (Currently Amended)** The method of Claim 25 wherein the ion source is mounted on the ~~target~~ electron gun carrier.

**27. (Currently Amended)** The method of Claim 25 further comprising the step of positioning a second ~~target~~ electron gun on the ~~target~~ electron gun carrier, the second ~~target~~ electron gun being adapted to provide energy for evaporation of a second material to be deposited on the substrates and being positionable at the source deposition location and the stand-by location.

**28. (New)** The method of Claim 1 wherein the stand-by location is laterally spaced from the ion source a distance greater than the distance the source deposition location is spaced from the ion source.